

General Description

The AOZ8222DI-05 is a two-line transient voltage suppressor diode designed to protect voltage sensitive electronics from high transient conditions and ESD.

This device incorporates two TVS diodes in an ultra-small DFN 1.0 x 0.6 package. During transient conditions, the TVS diodes direct the transient to ground. The AOZ8222DI-05 may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (± 15 kV air, ± 8 kV contact discharge).

The AOZ8222DI-05 comes in an RoHS compliant 3-lead DFN package and is rated over a -40°C to $+85^{\circ}\text{C}$ ambient temperature range.

The ultra-small 1.0 mm x 0.6 mm x 0.5 mm DFN package makes it ideal for applications where PCB space is a premium. The small size and high ESD protection makes it ideal for protecting voltage sensitive electronics from high transient conditions and ESD.

Features

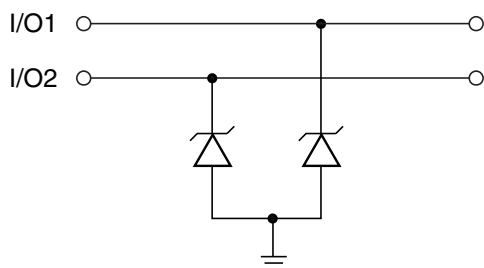
- ESD protection for high-speed data lines:
 - Exceeds IEC 61000-4-2 (ESD): ± 20 kV (air), ± 20 kV (contact)
 - Human Body Model (HBM) ± 30 kV
- Small package saves board space
- Low insertion loss
- Low clamping voltage
- Low operating voltage: 5 V

Applications

- Portable handheld devices
- Keypads, data lines, buttons
- Notebook computers
- Digital Cameras
- Portable GPS
- MP3 players

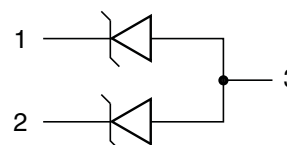


Typical Application



Unidirection Protection of Two Line

Pin Configuration



Ordering Information

Part Number	Ambient Temperature Range	Package	Environmental
AOZ8222DI-05	-40 °C to +85 °C	DFN 1.0 x 0.6-3L	Green Product



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant.
 Please visit www.aosmd.com/media/AOSGreenPolicy.pdf for additional information.

Absolute Maximum Ratings

Exceeding the Absolute Maximum ratings may damage the device.

Parameter	AOZ8222DI-05DI-05
Peak Pulse Current, $t_p = 8/20 \mu s$	5.5 A
Peak Pulse Power, $t_p = 8/20 \mu s$	50 W
Storage Temperature (T_S)	-65 °C to +150 °C
ESD Rating per IEC61000-4-2, Contact ⁽¹⁾	± 20 kV
ESD Rating per IEC61000-4-2, Air ⁽¹⁾	± 20 kV
ESD Rating per Human Body Model ⁽²⁾	± 30 kV

Notes:

- IEC 61000-4-2 discharge with $C_{Discharge} = 150 \text{ pF}$, $R_{Discharge} = 330 \Omega$.
- Human Body Discharge per MIL-STD-883, Method 3015 $C_{Discharge} = 100 \text{ pF}$, $R_{Discharge} = 1.5 \text{ k}\Omega$.

Maximum Operating Ratings

Parameter	Rating
Junction Temperature (T_J)	-40 °C to +125 °C

Electrical Characteristics

$T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

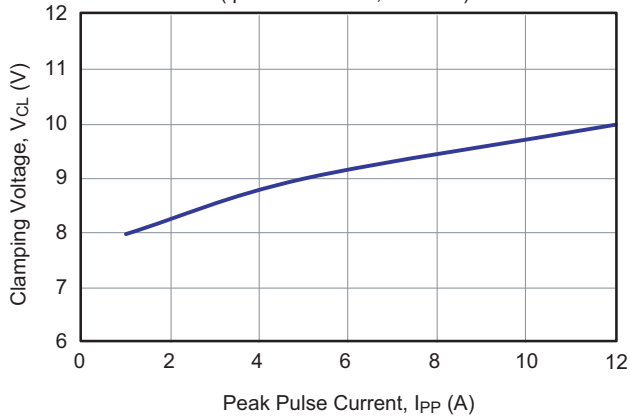
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V_{RWM}	Reverse Working Voltage	Between I/O and $V_N^{(3)}$			5.0	V
V_{BR}	Reverse Breakdown Voltage	$I_T = 1\text{ mA}$, between I/O and $V_N^{(4)}$	6.0			V
I_R	Reverse Leakage Current	$V_{RWM} = 5\text{ V}$, between I/O and V_N			1	μA
V_F	Diode Forward Voltage	$I_F = 10\text{ mA}$	0.6	0.7	0.9	V
V_{CL}	Channel Clamp Voltage Positive Transients Negative Transients	$I_{PP} = 1\text{ A}$, $t_p = 100\text{ ns}$, any I/O pin to Ground ⁽⁵⁾⁽⁶⁾			8.0 -2.0	V V
	Channel Clamp Voltage Positive Transients Negative Transients	$I_{PP} = 5\text{ A}$, $t_p = 100\text{ ns}$, any I/O pin to Ground ⁽⁵⁾⁽⁶⁾			9.0 -5.0	V V
	Channel Clamp Voltage Positive Transients Negative Transients	$I_{PP} = 12\text{ A}$, $t_p = 100\text{ ns}$, any I/O pin to Ground ⁽⁵⁾⁽⁶⁾			10.0 -10.0	V V
C_J	Channel Input Capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, between I/O pins ⁽⁶⁾		8	9	pF
		$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, any I/O pin to Ground ⁽⁶⁾		15	18	pF

Notes:

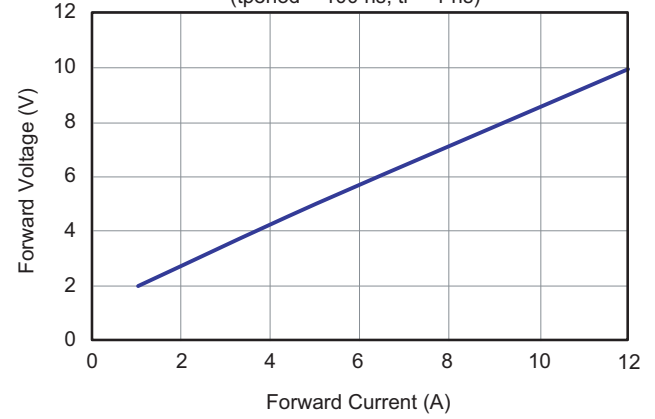
- The working peak reverse voltage, V_{RWM} , should be equal to or greater than the DC or continuous peak operating voltage level.
- V_{BR} is measured at the pulse test current I_T .
- Measurements performed using a 100ns Transmission Line Pulse (TLP) system.
- Guaranteed by design and characterization.

Typical Performance Characteristics

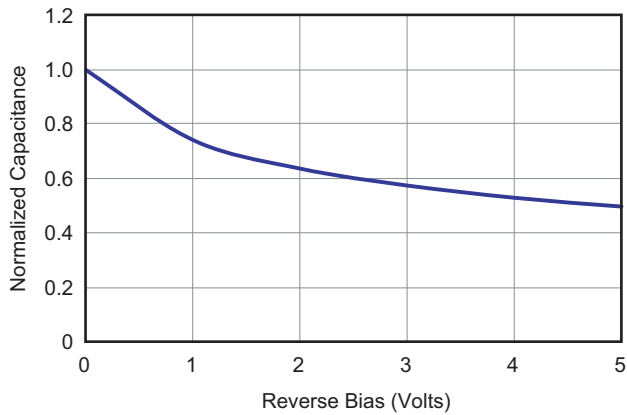
Clamping Voltage vs. Peak Pulse Current
(tperiod = 100 ns, tr = 1 ns)



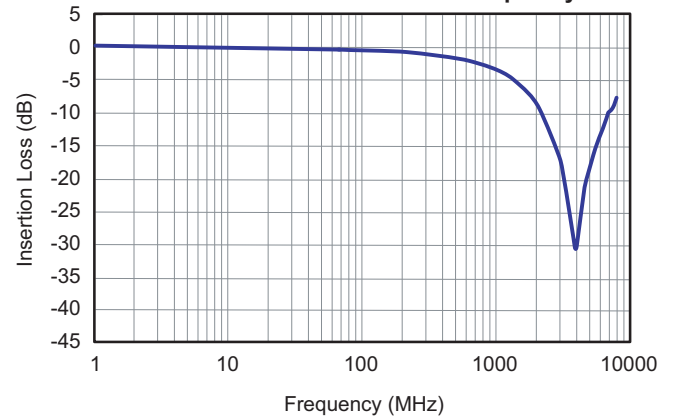
Forward Voltage vs. Forward Current
(tperiod = 100 ns, tr = 1 ns)

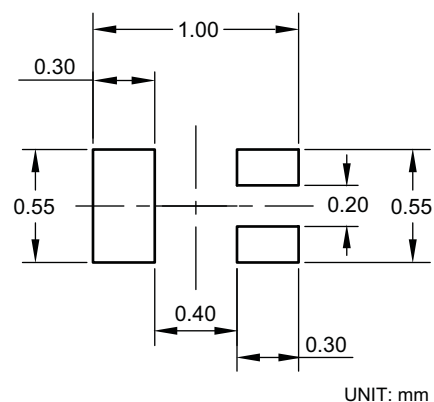
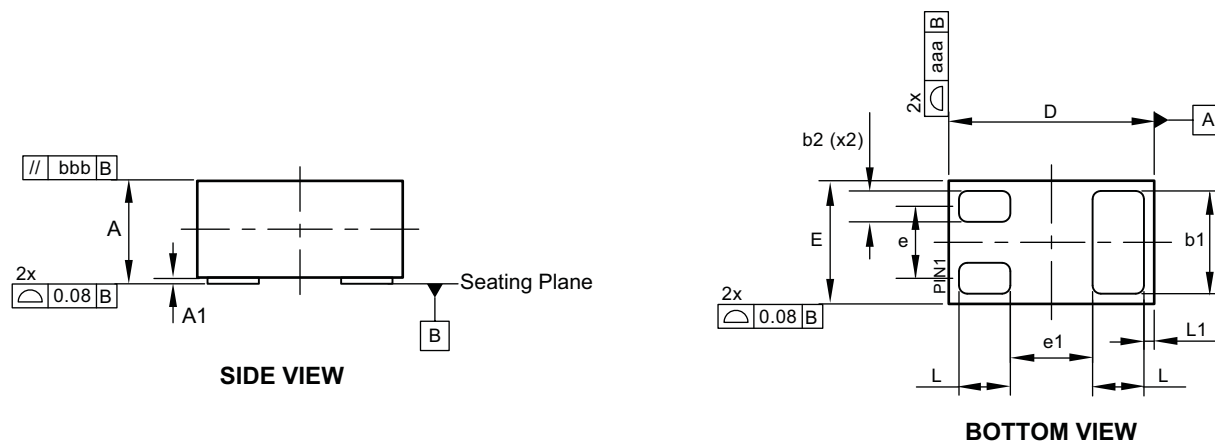


Capacitance vs. Reverse Bias



I/O – Gnd Insertion Loss vs. Frequency





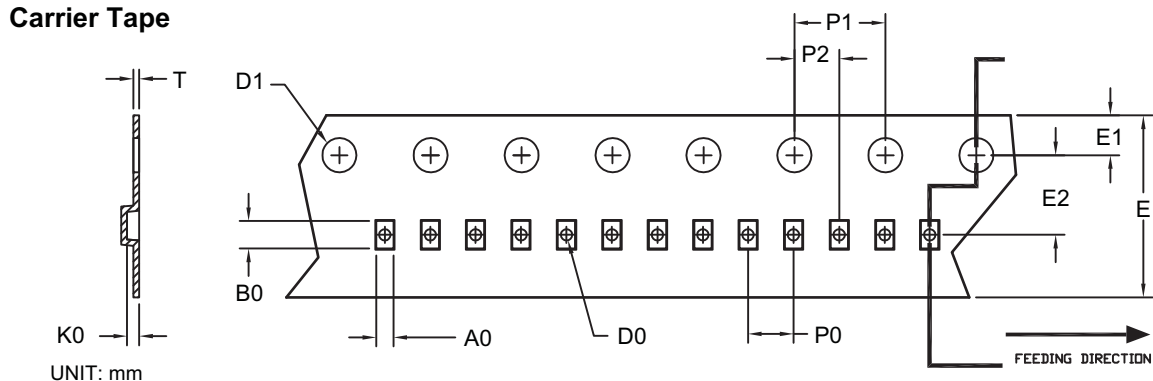
Symbols	Min.	Nom.	Max.
A	0.50	0.52	0.55
A1	0.00	0.03	0.05
b1	0.45	0.50	0.55
b2	0.10	0.15	0.20
D	0.95	1.00	1.075
E	0.55	0.60	0.675
e	---	0.35	---
e1	---	0.40	---
L	0.20	0.25	0.30
L1	---	0.05	---
aaa	0.15		
bbb	0.05		

Symbols	Min.	Nom.	Max.
A	0.019	0.020	0.022
A1	0.000	0.001	0.002
b	0.018	0.020	0.022
b2	0.004	0.006	0.008
D	0.037	0.039	0.042
E	0.022	0.024	0.027
e	---	0.014	---
e1	---	0.016	---
L	0.008	0.010	0.012
L1	---	0.002	---
aaa	0.006		
bbb	0.002		

1. All dimensions are in milliteters. Angles are in degrees.
- 2.Coplanarity applies to the exposed heat sink slug as well as the terminals.

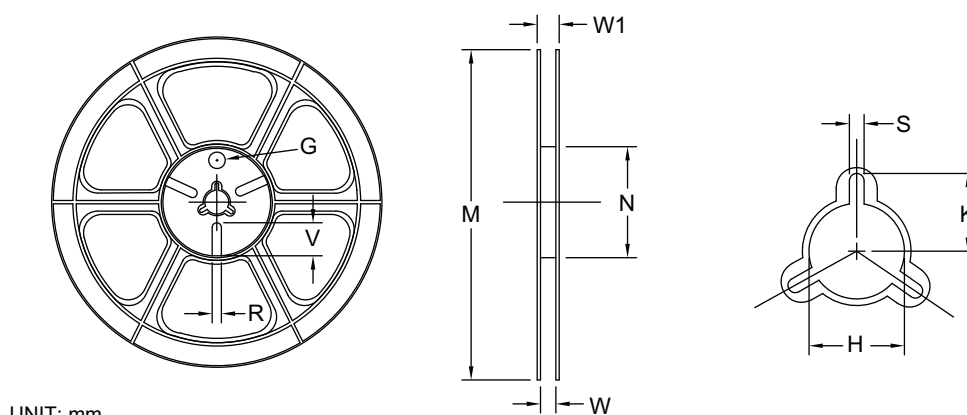
Tape and Reel Dimensions, DFN 1.0 x 0.6

Carrier Tape



Option	Package	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
A	DFN 1.0x0.6/ DFN 1.0x0.6A (8 mm)	0.69 ±0.05	1.19 ±0.05	0.66 ±0.05	0.40 ±0.05	1.50 ±0.10	8.00 +0.3/-0.1	1.75 ±0.10	3.50 ±0.05	2.00 ±0.05	4.00 ±0.10	2.00 ±0.05	0.23 ±0.02
B	DFN 1.0x0.6/ DFN 1.0x0.6A (8 mm)	0.65 ±0.04	1.05 ±0.04	0.61 ±0.04	0.40 ±0.05	1.50 ±0.10	8.00 +0.3/-0.1	1.75 ±0.10	3.50 ±0.05	2.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.05

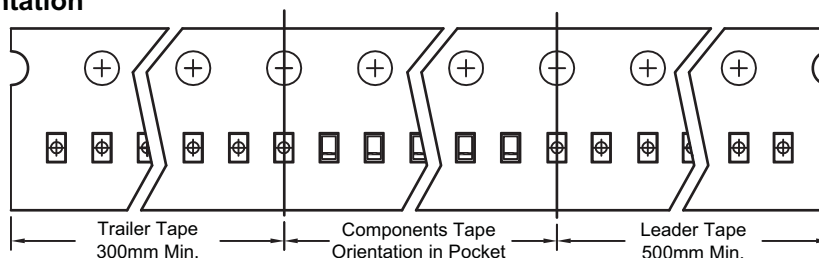
Reel



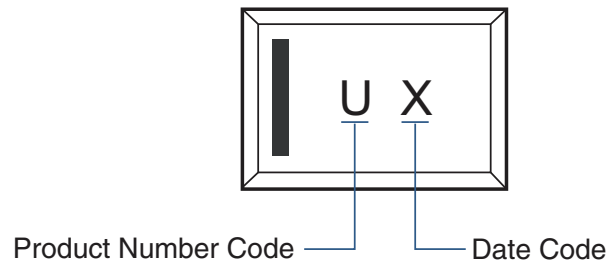
Tape Size	Reel Size	M	N	W	W1	H	K	S	G	R	V
8mm	ø178	ø178 ±0.5	ø55 ±1	8.4 +1.5/-0	Max. 14.4	ø13.0 ±0.5	Max. 10.1	2.0 ±0.5	N/A	N/A	N/A

Leader / Trailer & Orientation

TVS
Unit Per Reel:
10000pcs



Part Marking



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